Switching (60V, 300mA) **RK7002A**

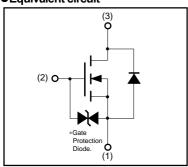
Features

- 1) Low on-resistance.
- 2) High ESD
- 3) High-speed switching.
- 4) Low-voltage drive (4V).
- 5) Easily designed drive circuits.
- 6) Easy to use in parallel.

Structure

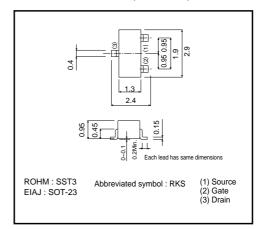
Silicon N-channel MOSFET transistor

Equivalent circuit



* A protection diode has been built in between the gate and the source to protect against static electricity when the product is in use.
Use the protection circuit when fixed voltages are

●External dimensions (Units : mm)



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage	rain-source voltage		60	V
Gate-source voltage		Vgss	±20	V
	Continuous	ΙD	300	mA
Drain current	Pulsed	IDP*1 1.2	А	
Drain reverse current	Continuous	IDR	300	mA
	Pulsed	IDRP*1	1.2	А
Total power dissipation	n	Po*2	200 mW	
Channel temperature		Tch	150	°C
Storage temperature		Tstg	_55~+150 °C	

^{*1} Pw≤10μs, Duty cycle≤1% *2 When using 1×0.75×0.062 inch glass epoxy board.

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Gate leakage current	lgss	-	-	±10	μΑ	Vgs=±20V, Vps=0V	
Drain-source breakdown voltage	V (BR) DSS	60	_	-	V	I _D =10μA, V _G s=0V	
Drain cutoff current	Ipss	_	-	1	μΑ	VDS=60V, VGS=0V	
Gate threshold voltage	VGS (th)	1	_	2.5	V	V _{DS} =10V, I _D =1mA	
Drain-source on-state resistance	RDS (on)*1	_	0.7	1.0	Ω	ID=300mA, Vgs=10V	
		-	1.1	1.5		ID=300mA, VGS=4V	
Forward transfer admittance	I Yfs I*1	200	-	-	mS	V _{DS} =10V, I _D =300mA	
Input capacitance	Ciss	_	33	-	pF	Vps=10V	
Output capacitance	Coss	-	14	-	pF	V _{GS} =0V f=1MHz	
Reverse transfer capacitance	Crss	_	9	-	pF		
Turn-on delay time	td (on)*2	-	6	-	ns	I _D =150mA, V _{DD} =30V V _{GS} =10V R _L =200Ω R _{GS} =10Ω	
Rise time	tr*2	_	5	-	ns		
Turn-off delay time	td (off)*2	-	13	-	ns		
Fall time	tr*2	-	80	-	ns		
Total gate charge	Qg*2	_	3	6	nC	V _{DD} ≒30V	
Gate-source charge	Q _{gs} *2	-	0.6	-	nC	V _{GS} =10V I _D =200mA	
Gate-drain charge	Q _{gd} *2	-	0.5	-	nC		

^{*1} Pw≤300μs, Duty cycle≤1% *2 Pulsed

Packaging specifications

	Package	Taping
	Code	T116
Type	Basic ordering unit (pieces)	3000
RK7002A		0

• Electrical characteristic curves

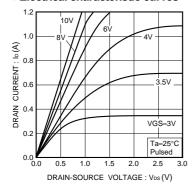


Fig.1 Typical output characteristics

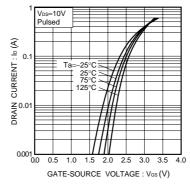


Fig.2 Typical transfer characteristics

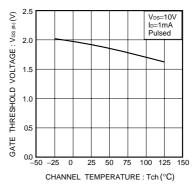
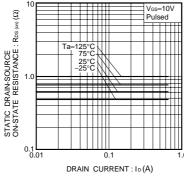
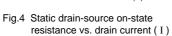


Fig.3 Gate threshold voltage vs. channel temperature





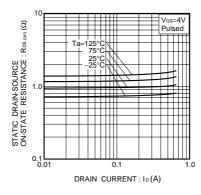


Fig.5 Static drain-source on-state resistance vs. drain current (II)

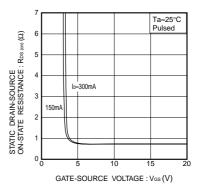


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

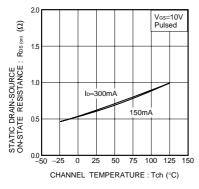


Fig.7 Static drain-source on-state resistance vs. channel temperature

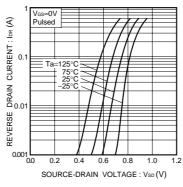


Fig.8 Reverse drain current vs. source-drain voltage (I)

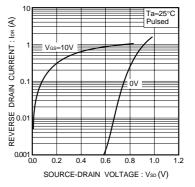


Fig.9 Reverse drain current vs. source-drain voltage (II)

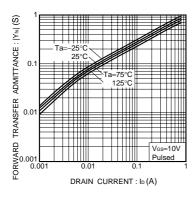


Fig.10 Forward transfer admittance vs. drain current

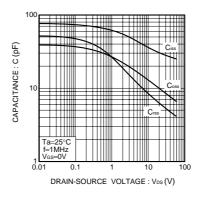


Fig.11 Typical capacitance vs. drain-source voltage

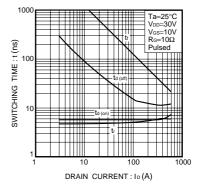


Fig.12 Switching characteristics (See Figures 13 and 14 for the measurement circuit and resultant waveforms)

•Switching characteristics measurement circuit

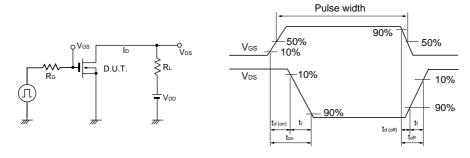


Fig.13 Switching time measurement circuit

Fig.14 Switching time waveforms

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